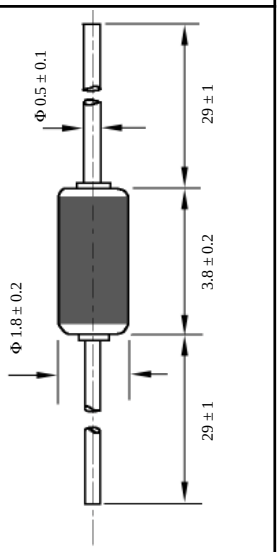
BI-DIRECTIONAL TRIGGER DIODES

DO-35 玻壳封装双向触发二极管

DO-35 GLASS-SEALED BI-DIRECTIONAL TRIGGER DIODES

符 号 Symbol	参 数 Parameter	测试条件 Test Condition	型 号 Type	Min	Typ	Max	Unit	外 型 尺 寸 Package（单位：mm）
V_{BO}	击穿电压 Breakdown Voltage	见图 1 See Fig 1	DB-3 DB-4 DB-6	28 35 56	32 40 60	36 45 70	V	 DO – 35 (mm)
$\lvert +V_{BO} \rvert - \lvert -V_{BO} \rvert$	击穿电压对称性 Breakover Voltage Symmetry	见图 1 See Fig 1	DB-3 DB-4 DB-6			3 3 4	V	
$\lvert \pm \Delta V \rvert$	动态回弹电压 Dynamic Breakback Voltage	$\Delta I = \lvert I_{BO}$ to I_F=10mA$\rvert$ See Fig 1	DB-3 DB-4 DB-6	5 5 10			V	
V_O	输出电压 Output Voltage	见图 2 See Fig 2		5			V	
I_{BO}	击穿电流 Breakdown Current					100	μA	
t_r	上升时间 Rise Time	见图 3 See Fig 3			1.5		μS	
I_B	漏电流 Leakage Current	Vm=0.5V_{BO}(Max) 见图 1 See Fig 1				10	μA	

极限参数

LIMITING VALUES

符 号 Symbol	参 数 Parameter		Value		Unit
P_C	功耗 Power Dissipation	t_a=50°C	150		mW
I_{Fmax}	峰值脉冲电流 Peak Pulse Current	t_p=10μs 120pps $T_a \leq$ 40°C	DB-3	2.0	A
			DB-4	2.0	
			DB-6	16	
T_r T_J	贮存与工作结温范围 Storage and Operating Junction Temperatuer Range		40 to 125 40 to 110		℃

DO-35 玻壳封装双向触发二极管特性曲线
DO-35 GLASS-SEALED BI-DIRECTIONAL TRIGGER DIODE

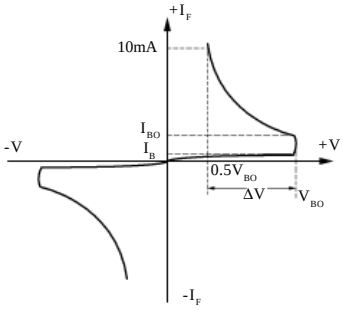


FIG-1 I - V 特性曲线
Current - voltage characterisitics

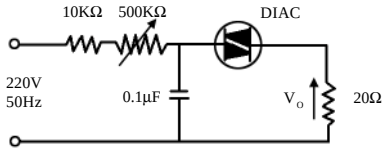


FIG-2 输出电压测试电路
Test circuit for output voltage

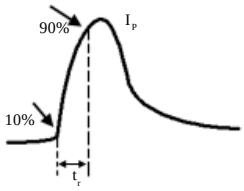


FIG-3 测试电路见图 2,调整 R, I_P=0.5A
Test circuit see diagram 2. Adjust R for I =0.5A

load up to 1500 watts

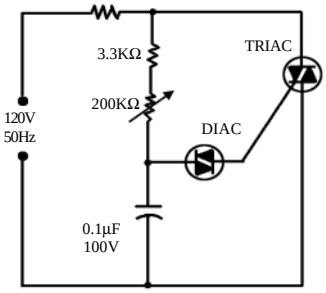


FIG-4 典型 DIAC-TRIAC 全波相控电路
Typical DIAC-TRIAC full-wave Phase control

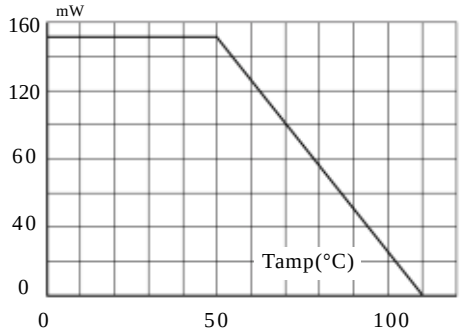


FIG-5 功耗环境温度关系曲线（最大值）
Power dissipation versus ambient temperature(maximum values)

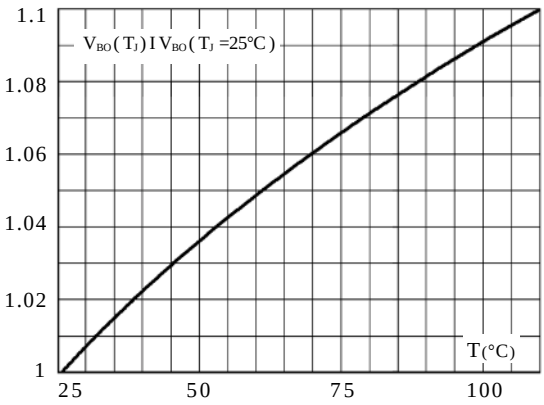


FIG-6 V_{BO} 的相对变化与结温关系曲线（典型值）
Relative variation of V_{BO} versus junction temperature (typical values)

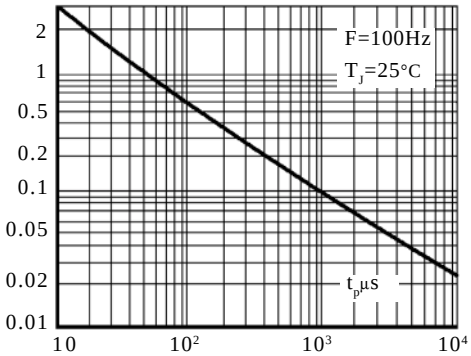


FIG-7 峰值脉冲电流与脉冲宽度关系曲线（最大值）
Peak pulse Current versus pulse duration (maximum values)